								F	REVISI	ONS										
L查询"5962R8512701VXA"供应商ESCRIPTION										DA	ATE (Y	(YR-MO-DA)			APPROVED					
A	Add two packages, C-5 and C-4. Make changes to table I, and case X, the dimensions have been changed and figure 2 has with D-10 configuration. Inactivate devices 01XX and 02XX for Use M38510 device. Add a truth table.						s been	replace	d	90-01-24				M. A. Frye						
В	Add device types 05, 06, 07, and 08. Add vendors CAGES 1ES66, OH9K9, and 33256. Editorial changes throughout.								9,		93-0	03-15	3-15 M. A. Frye							
С	Add o	class V	device	es. Add	I Z pac	kage.	Editoria	al chang	ges thro	oughou	t.			97-(	04-15			R. N	Ionnin	
D	Char	iges in	accord	lance w	vith NO	R 5962	-R368-	-97. – d	lrw					97-0	06-23		F	Raymor	nd Moni	nin
E				e desig prial cha						2-F28	to			99-1	12-30		F	Raymor	nd Moni	nin
F	Shee	et 7, tab	le I, V <sub>II</sub>	test, c	hange	max lin	nit from	n –0.8 V	′ to 0.8	V dry	N			00-0	03-01		F	Raymor	nd Moni	nin
G	Add i	radiatio	n featu	ires and	d post i	rradiati	on limi	ts dr	w					01-0	05-16		F	Raymor	nd Moni	nin
THE ORIGINAI REV SHEET REV	_ FIRS	T PAG	E OF	THIS C	G	NG HA	AS BEI			D										
SHEET	15	16	17	18	19	20														
REV STATUS				REV	/		G	G	G	G	G	G	G	G	G	G	G	G	G	G
OF SHEETS				SHE	ET		1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A				PRE	PARED	BY														
					Sa	andra E	3. Roor	ney			וח	FFFN	SE SI	IPPI	Y CE				us	
STAN	STANDARD			CHECKED BY				DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216												
	MICROCIRCUIT DRAWING					http://www.dscc.dla.mil														
	APPROVED BY					1														
FOR US	THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS				ſ	Vichae	I A. Fry	re		MICROCIRCUIT, LINEAR, MICROPROCESSOR COMPATIBLE, 12-BIT ANALOG-TO-DIGITAL										
AND AGEN DEPARTMEN				DRA	WING	APPRC 86-0	0VAL E 17-10	DATE		CO	NVE	RTEF	RS, MONOLITHIC SILICON							
AMS	SC N/A			REV	ISION	LEVEL				SI	ZE	CA	GE CC	DDE				<b>a-</b>	_	
						(	3				A		67268	3		;	5962 <sup>.</sup>	-8512	27	
						SHEET 1 OF 20														

DSCC FORM 2233 APR 97

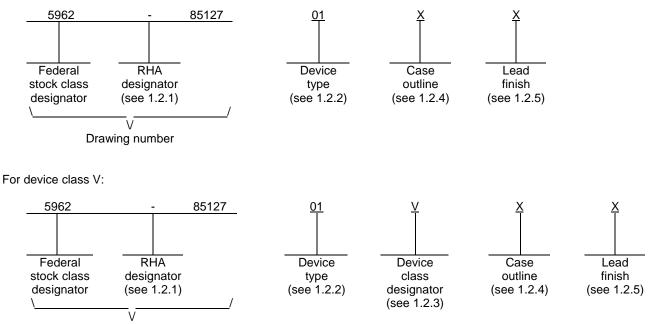
DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

### 1. SCOPE

查询"5962R8512701VXA"供应商 <del>1.1\_<u>Scope</u>. This drawing documents tw</del>o product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following examples.

For device classes M and Q:



Drawing number

1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 <u>Device types</u>. The device types identify the circuit function as follows:

Device type	Generic number	Circuit function
01	574AU	Monolithic, high performance, 12-bit A/D converter with microprocessor interface
02	574AT	Monolithic, medium performance, 12-bit A/D converter with microprocessor interface
03	574AU	Multi-chip, high performance, 12-bit A/D converter with microprocessor interface
04	574AT	Multi-chip, medium performance, 12-bit A/D converter with microprocessor interface
05	574ZA	Monolithic, high performance, low power, 12-bit A/D converter with microprocessor interface
06	574ZB	Monolithic, medium performance, low power, 12-bit A/D converter with microprocessor interface
07	574AU	Monolithic, high performance, low power, 12-bit A/D converter with microprocessor interface
08	574AT	Monolithic, medium performance, low power, 12-bit A/D converter with microprocessor interface

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1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as listed be 如何的问题的意义,我们就能帮助你的问题。 这些你们的意义,我们就能帮助你的问题。 designators will not be included in the PIN and will not be marked on the device.

Device class	Device requirements documentation						
М	Vendor self-certification to the requirements for MIL-STD-883 compliant, n JAN class level B microcircuits in accordance with MIL-PRF-38535, apper						
Q or V	Certification and qualification to MIL-PRF-38535						
1.2.4 Case outlines.	. The case outlines are as designated in MIL-STD-1835 and as follows:						
Outline letter	Descriptive designator	Terminals	Package style				
X Y	GDIP1-T28 or CDIP2-T28 CQCC1-N44	28 44	dual-in-line square leadless chip carrier				

flat pack

square leadless chip carrier

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

28

28

1.3 Absolute maximum ratings. 1/

Ζ

3

CDFP3-F28

CQCC1-N28

$V_{CC}$ to digital common $V_{EE}$ to digital common $V_{LOG}$ to digital common Analog to digital common:	0 to -16.5 V dc
Device types 01, 02, 03, 04 Device types 05, 06, 07, 08 Control inputs (CE, CS, A <sub>0</sub> , 12/8, R/C) to digital common Analog inputs (REF IN, BIP OFF, 10 V <sub>IN</sub> ) to analog common 20 V <sub>IN</sub> analog input voltage to analog common V <sub>REF OUT</sub>	-0.5 V dc to +1 V dc -0.5 V dc to V <sub>LOG</sub> +0.5 V dc V <sub>EE</sub> to V <sub>CC</sub> <u>+</u> 24 V dc
Power dissipation at 75°C:	
Device types 01, 02, 05, 06, 07, 08 Device types 03, 04	1,000 mVV <u>2</u> / 2,080 mW 2/
Lead temperature (soldering, 10 seconds)	
Storage temperature	
Thermal resistance, junction-to-ambient ( $\theta_{JA}$ ):	
Cases X and 3	70°C/W
Case Y	38°C/W
Case Z	60°C/W
Thermal resistance, junction-to-case ( $\theta_{JC}$ )	See MIL-STD-1835
Junction temperature (T <sub>J</sub> )	+175°C

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

 $\underline{2}$ / For cases X and 3, derate linearly above T<sub>A</sub> = +75°C at 20.8 mW/°C. For cases Y, derate linearly above T<sub>A</sub> = +75°C at 22.7 mW/°C. For cases Z, derate linearly above T<sub>A</sub> = +115°C at 17 mW/°C.

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<ul> <li>1.4 <u>Recommended operating conditions</u>.</li> <li>查询"5962R8512701VXA"供应商 Power supply</li> <li>Operating voltage range: Positive supply (V<sub>LOG</sub>) Positive supply (V<sub>CC</sub>) Negative supply (V<sub>EE</sub>) Ambient operating temperature range</li> <li>1.5 Radiation features</li> </ul>	+11.4 V dc to +16.5 V dc -11.4 V dc to -16.5 V dc
Maximum total dose available (dose rate = 50 – 300 rad/s)	≤100 Krads

### 2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

### SPECIFICATION

### DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

### STANDARDS

### DEPARTMENT OF DEFENSE

MIL-STD-883	-	Test Method Standard Microcircuits.
MIL-STD-1835	-	Interface Standard Electronic Component Case Outlines.

### HANDBOOKS

### DEPARTMENT OF DEFENSE

MIL-HDBK-103 - List of Standard Microcircuit Drawings. MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

### 3. REQUIREMENTS

3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

	1	I	
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3.2.1 <u>Case outlines</u>. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.2.3 <u>Truth table</u>. The truth table shall be as specified on figure 2.

3.2.4 <u>Block or logic diagrams</u>. The block or logic diagrams shall be as specified on figure 3.

3.2.5 <u>Radiation exposure circuit</u>. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.

3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 <u>Notification of change for device class M</u>. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-PRF-38535, appendix A.

3.9 <u>Verification and review for device class M</u>. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 81 (see MIL-PRF-38535, appendix A).

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<u>查询"5962R8512701VX</u>		Conditions	.e					
Test	Symbol	$-55^{\circ}C \le T_{A} \le +125^{\circ}C$ $V_{CC} = +15 V, V_{LOG} = +5 V,$ $V_{EE} = -15 V $ <u>1</u> /		Group A subgroups	Device type	Lim	iits	Unit
	l	unless otherwise s	specified		[	Min	Max	
Power supply current From V <sub>LOG</sub>	ILOG			1, 2, 3	01, 02, 03, 04		40	mA
	l	Μ,	D, L, R	1	02		40	
				1, 2, 3	05, 06, 07, 08		1	
Power supply current	Icc			1, 2, 3	01, 02		5	mA
From V <sub>CC</sub>	l	M,	D, L, R	1	02		5	
	l	_		1, 2, 3	03, 04		15	
					05, 06, 07, 08		9	
Power supply current	IEE			1, 2, 3	01, 02, 03, 04	-30		mA
From V <sub>EE</sub>	l	М,	D, L, R	1	02	-30		
				1, 2, 3	05, 06, 07, 08	0		
Resolution	ĺ			1, 2, 3	All	12		Bits
Integral linearity error	ILE			1	All	-0.5	0.5	LSB
				2, 3		-1.0	1.0	
		M,	D, L, R	1	02	-1.0	1.0	
Differential linearity error (minimum resolution for	DLE			1	All	12		Bits
which no missing codes guaranteed) <u>2</u> /			ł	2, 3		12		
Unipolar offset voltage error	V <sub>IO</sub>	T <sub>A</sub> = +25°C		1	All	-2.0	2.0	LSB
		М,	D, L, R	1	02	-3.0	3.0	
				12	01	-1.0	1.0	
Unipolar offset drift <u>2</u> /	<u>ΔV<sub>IO</sub></u> ΔT	Using internal refe	rence	2, 3	All	-1.0	1.0	LSB
Bipolar offset voltage error	Bz	T <sub>A</sub> = +25°C		1	All	-4.0	4.0	LSB
		М,	D, L, R	1	02	-5.0	5.0	
				12	01	-2.0	2.0	
Bipolar zero offset drift <u>2</u> /	$\frac{\Delta B_Z}{T}$	Using internal refe	rence	2, 3	01, 03, 05, 07	-1.0	1.0	LSB
_					02, 04, 06, 08	-2.0	2.0	

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查询"5962R8512701VX		<ol> <li>Electrical performance chara</li> </ol>	<u>acteristics</u> – co	intinuea.			
Test	Symbol	$\begin{array}{c} \mbox{Conditions} \\ -55^{\circ}\mbox{C} \leq T_{A} \leq +125^{\circ}\mbox{C} \\ \mbox{V}_{CC} = +15 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	Group A subgroups	Device type	Lin	nits	Unit
		unless otherwise specified			Min	Max	
Gain error	$\Delta A_E$	T <sub>A</sub> = +25°C	1	01, 02		0.25	% of
		M, D, L, R	1	02		0.35	F.S.
		With $50\Omega$ resistor from	1	03, 04,		0.30	
		REF OUT to REF IN		05, 06,			
			40	07, 08	 	0.405	4
			12	01	10 5	0.125	
Gain error drift	$\Delta A_E$	Using internal reference	2, 3	01, 03,	-12.5	12.5	ppm/°C
<u>2</u> /	ΔT			05, 07	25.0	05.0	4
				02, 04,	-25.0	25.0	
	+P <sub>SS1</sub>	+13.5 V ≤ V <sub>CC</sub> ≤ +16.5 V	1	06, 08 All	-1.0	1.0	LSB
Power supply sensitivity	+rss1	$+13.5 \text{ V} \leq \text{V}_{CC} \leq +16.5 \text{ V}$ $T_A = +25^{\circ}\text{C}$	I	All	-1.0	1.0	LOD
(Maximum change in	+P <sub>SS2</sub>	$T_A = +25^{\circ}C$ +11.4 V $\leq V_{CC} \leq +12.6$ V	-				
full scale calibration)	+ <b>F</b> \$\$2	$+11.4 \text{ V} \leq \text{V}_{CC} \leq +12.6 \text{ V}$ $T_A = +25^{\circ}\text{C}$					
<u>2</u> /	+P <sub>SS3</sub>	A = +25  C +4.5 V $\leq$ V <sub>LOG</sub> $\leq$ +5.5 V	1	All	-0.5	0.5	1
	TI 553	$T_A = +25^{\circ}C$			-0.0	0.5	
	-P <sub>SS1</sub>	-16.5 V ≤ V <sub>EE</sub> ≤ -13.5 V	1	All	-1.0	1.0	-
	-1 221	$T_{A} = +25^{\circ}C$		- <u> </u>	-1.0	1.0	
	-P <sub>SS2</sub>	$-12.6 V \le V_{EE} \le -11.4 V$	4				
	1 002	$T_A = +25^{\circ}C$					
Input Impedance	Z <sub>IN</sub>	10 V span, $T_A = +25^{\circ}C$	4	All	3	7	kΩ
<u>2</u> /		20 V span, $T_A = +25^{\circ}C$	4	01, 02,	6	14	
<u> </u>				03, 04	-		
				05, 06,	15	25	•
				07, 08			
nternal reference voltage	V <sub>REF</sub>	$T_{A} = +25^{\circ}C$ <u>3</u> /	1	01, 02	9.98	10.02	V
C C		 M, D, L, R	1	02	9.95	10.05	•
			1	03, 04	9.90	10.10	1
				07, 08			
				05, 06	9.97	10.03	
			12	01	9.99	10.01	
Output current	lo	Available for external loads	1	01, 02,		1.5	mA
<u>2</u> /, <u>4</u> /		$T_A = +25^{\circ}C$		03, 04			
				05, 06,		2.0	
				07, 08			
ee footnotes at end of table.							
STA	NDARD	SI	ZE			596	

MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000

本沟"500000540704\//		. Electrical performation	nce char	acteristics	<u>-</u> contir	nued.			
<u>查询"5962R8512701VX</u> Test	A_1共办业际 Symbol	Conditions			)evice /pe	Lin	nits	Unit	
		unless otherwise sp	ecified				Min	Max	
Input voltage (CE, <del>CS,</del> 12/8, R/C, A <sub>0</sub> ) <u>2/, 5/</u>	VIH	Logic "1", T <sub>A</sub> = +25°		1	0	1, 02, 5, 06, 07, 08	2.0	5.5	V
					C	03, 04	2.4	5.5	
	VIL	Logic "0", T <sub>A</sub> = +25°	С	1		All	-0.5	0.8	
Input current <u>2</u> /	I <sub>IN</sub>	T <sub>A</sub> = +25°C		1	0	1, 02, 3, 04, 07, 08	-20	+20	μA
					(	05,06	-1	1	
Output voltage (DB11-DB0, STS) <u>2</u> /	V <sub>OL</sub>	Logic "0", T <sub>A</sub> = +25° I <sub>SINK</sub> = +1.6 mA	С,	1		All		0.4	V
Output voltage (DB11-DB0) 2/	V <sub>OH</sub>	Logic "1", T <sub>A</sub> = +25° I <sub>SOURCE</sub> = +500 μA	Ċ,	1 1		All	2.4		V
High impedance state       output current     2/	Iz	High-Z state, T <sub>A</sub> = + DB11 – DB0 only	25°C,	1	0	1, 02, 3, 04, 07, 08	-20	+20	μΑ
					C	05, 06	-5	+5	
Functional tests		See 4.4.1b, T <sub>A</sub> = +2	5°C	7		All			
		See figure 4		9, 10,	11 0	01, 02	250		ns
Low $R/\overline{C}$ pulse width	t <sub>HRL</sub>					03, 04	350		
<u>2</u> /, <u>6</u> /						95, 06, 07, 08	50		
STS delay from R/ <del>C</del> <u>2</u> /, <u>6</u> /	t <sub>DS</sub>	See figure 4		9, 10,	0	1, 02, 03, 04 5, 06,		600 200	ns
Data valid after R/C low <u>2</u> /, <u>6</u> /	t <sub>HDR</sub>	See figure 4		9, 10,	11 0 0 0	07, 08 01, 02, 05, 06, 07, 08 03, 04	25		ns
STS delay after valid data <u>2</u> /, <u>6</u> /	tнs	See figure 4		9, 10,	0	1, 02, 5, 06, 07, 08 03, 04	300	1000	ns
High R/ <del>C</del> pulse width <u>2/, 7/</u>	t <sub>HRH</sub>	See figure 4		9, 10,	11 0 0	1, 02, 03, 04 05, 06,	300 300 150	1200	ns
See footnotes at end of table.						07, 08			
STAN MICROCIRCU	DARD JIT DRAV	VING		IZE <b>A</b>				5962	2-85127
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查询"5962R8512701VX		I. Electrical performance chara	<u>acteristics</u> – co	ntinued.			
<u>E10_5962R8512701VX</u> Test	A 1 <u>共加</u> 陷 Symbol	Conditions $-55^{\circ}C \le T_A \le +125^{\circ}C$ $V_{CC} = +15 V, V_{LOG} = +5 V,$ $V_{EE} = -15 V $ 1/	Group A subgroups	Device type	Limits		Unit
		unless otherwise specified			Min	Max	
Data access time <u>2</u> /, <u>7</u> /	t <sub>DDR</sub>	See figure 4	9, 10, 11	01, 02, 03, 04		250	ns
=, -				05, 06, 07, 08		150	
STS delay from CE <u>2/, 7/</u>	t <sub>DSC</sub>	See figure 4	9, 10, 11	01, 02, 03, 04		350	ns
=,_				05, 06, 07, 08		200	
CE pulse width <u>2/, 7/</u>	t <sub>HEC</sub>	See figure 5	9, 10, 11	01, 02, 03, 04	300		ns
				05, 06, 07, 08	50		
Conversion time	tc	8-bit cycle	9, 10, 11	01,02 <u>4</u> /	10	24	μs
<u>2</u> /, <u>8</u> /		See figure 5		03, 04, 05, 06, 07, 08	10	17	
		12-bit cycle	9, 10, 11	01,02 <u>4</u> /	15	35	
		See figure 5		03, 04, 05, 06, 07, 08	15	25	
Access time (from CE)	t <sub>DD</sub>	See figure 6	9, 10, 11	01, 02		200	ns
<u>2</u> /, <u>6</u> /				03, 04		250	
				05, 06, 07, 08		150	
Data valid after CE low <u>2</u> /, <u>6</u> /	t <sub>HD</sub>	See figure 6	9, 10, 11	01, 02, 05, 06, 07, 08	25		ns
		-		03, 04	15		
Output float delay	t <sub>HL</sub>	See figure 6	9, 10, 11	01, 02		100	ns
<u>2</u> /, <u>6</u> /				03, 04, 05, 06,		150	
				07, 08			

1/ Devices supplied to this drawing have been characterized through all levels M, D, L, and R of irradiation. However, this device is only tested at the "R" level. Pre and post irradiation values are identical unless otherwise specified in table I. When performing post irradiation electrical measurements for any RHA level,  $T_A = +25^{\circ}C$ .

2/ This parameter is not tested post irradiation. 3/ The reference voltage external load events The reference voltage external load current shall be a constant dc and shall not exceed 1.5 mA.

 $\frac{1}{4}$ / Reference should be buffered for operation on  $\pm 12$  V supplies. External load should not change during conversion.

5/ For devices 01 and 02, 12/8 is not TTL compatible and must be hard wired to V<sub>LOG</sub> or digital ground.

 $\underline{6}$ / Subgroups 10 and 11, if not tested, shall be guaranteed to the specified limits.

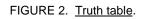
 $\underline{7}$  Parameters t<sub>HRH</sub>, t<sub>DDR</sub>, t<sub>DSC</sub>, and t<sub>HEC</sub>, if not tested, shall be guaranteed to the specified limits.

8/ For devices 03 and 04, time measured from 50 percent level of digital transitions, tested with 50 pF and 3.0 k $\Omega$  load.

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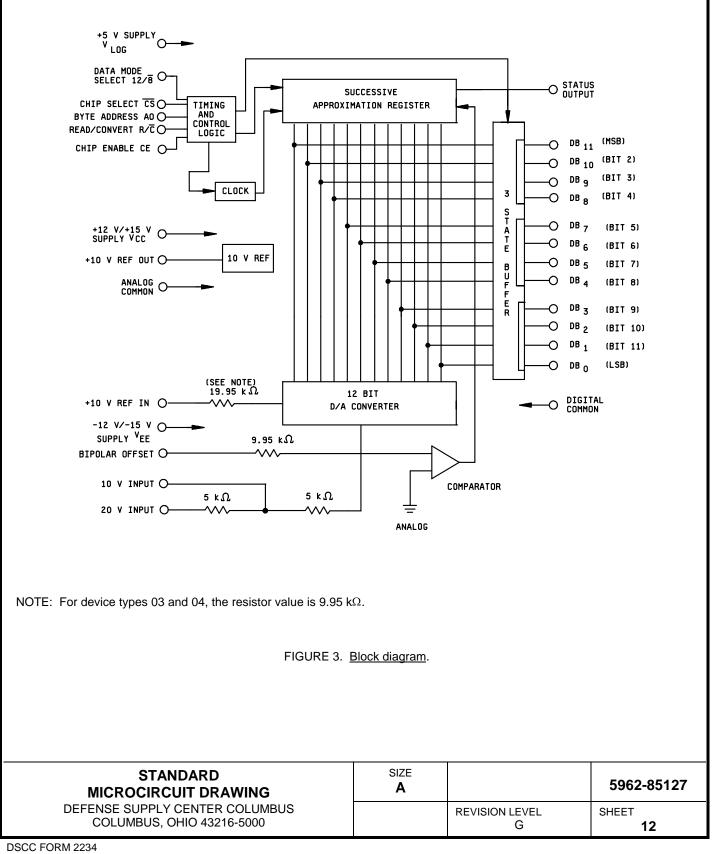
询"5962R8512700W)	(Atly 供应商	All	01, 02	01, 02, 05, 06, 07	7, 08	03, 04	
	outlines	Х	Z	3		Y	]
Termin	al number	·	Termi	nal symbol	Te	erminal symbol	]
	1			V <sub>LOG</sub>		V <sub>LOG</sub>	
	2	12/8				12/8	
	3			CS		CS	
	4			AO		AO	
	F			R/C			
	5			CE		NC	
	6 7			V <sub>cc</sub>		NC NC	
	8		DE			NC	
	9			AGND		R/C	
	9 10			REF IN		CE	
	11		r r	V <sub>EE</sub>		Vcc	
	12		BI			REF OUT	
	13			10 V <sub>IN</sub>		AGND	
	14			20 V <sub>IN</sub>		REF IN	
	15					VEE	
	16			DB0		NC	
	17			DB1		BIP OFF	
	18			DB2		10 V <sub>IN</sub>	
	19			DB3		20 V <sub>IN</sub>	
	20			DB4		NC	
	21			DB5		NC	
	22			DB6		NC	
	23			DB7		NC	
	24	DB8		DGND			
	25			DB9		NC	
	26		I	DB10		NC	
	27		DB1	1 (MSB)		DB0	
	28			STS		DB1	
	29					DB2	
	30					NC	
	31					DB3	
	32					DB4	
	33					DB5	
	34					DB6	
	35					DB7	
	36					DB8	
	37					DB9	
	38					NC	
	39					NC NC	
	40 41					NC NC	
	41 42					DB10	
	42 43					DB10 DB11 (MSB)	
	43					STS	
L	<del></del>					010	
		FIGU	RE 1. <u>Te</u>	rminal connections			
		NG		SIZE A			5962-851
	MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000				REVISION	N LEVEL	SHEET

CE	CS	R/C	 12/8	Ao	Operation
0	X	X	X	X	None
X	1	X	X	X	None
1	0	0	X	0	Initiate 12-bit conversion
1	0	0	X	1	Initiate 8-bit conversion
1	0	1	1	Х	Enable 12-bit parallel output
1	0	1	0	0	Enable 8 most significant bits
1	0	1	0	1	Enable 4 LSBs + 4 trailing zeros

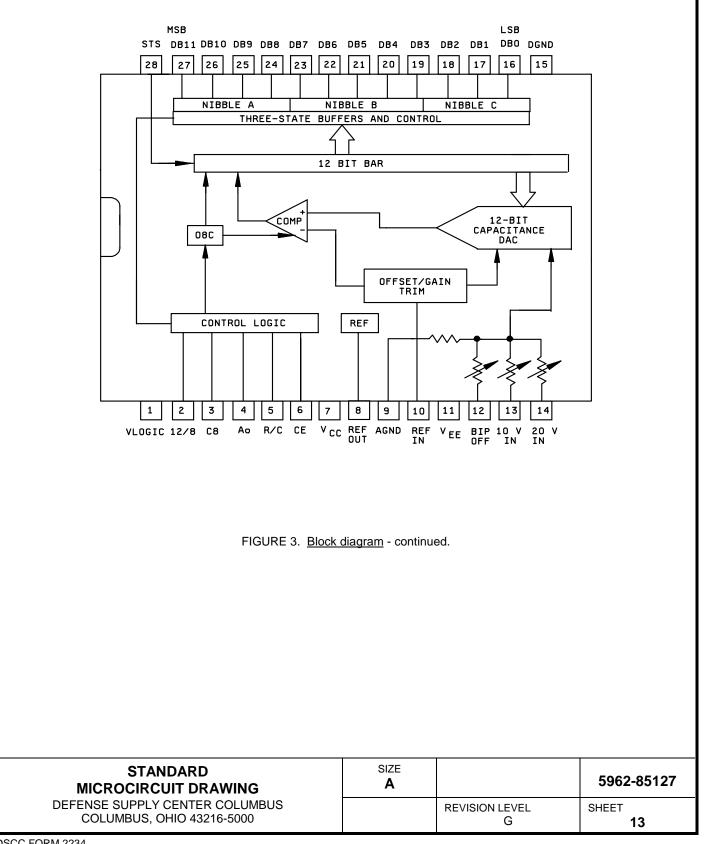


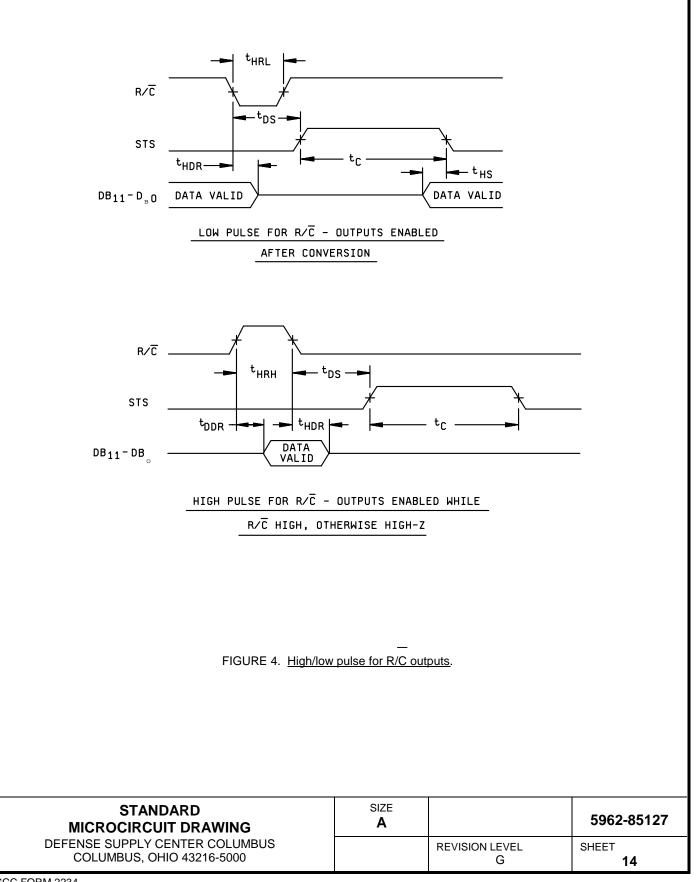
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-85127
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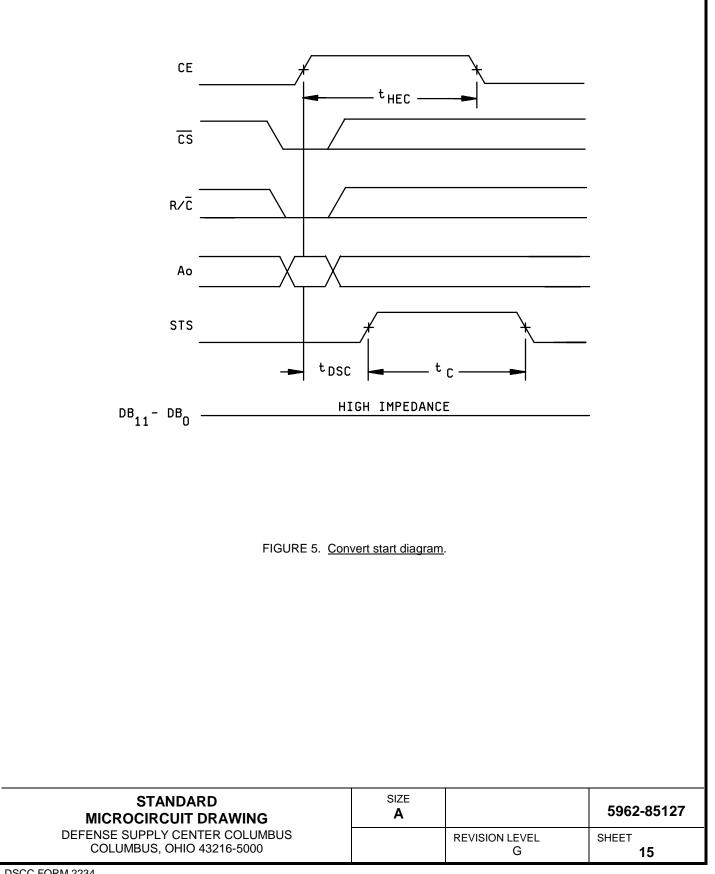
Device types 01, 02, 03, and 04

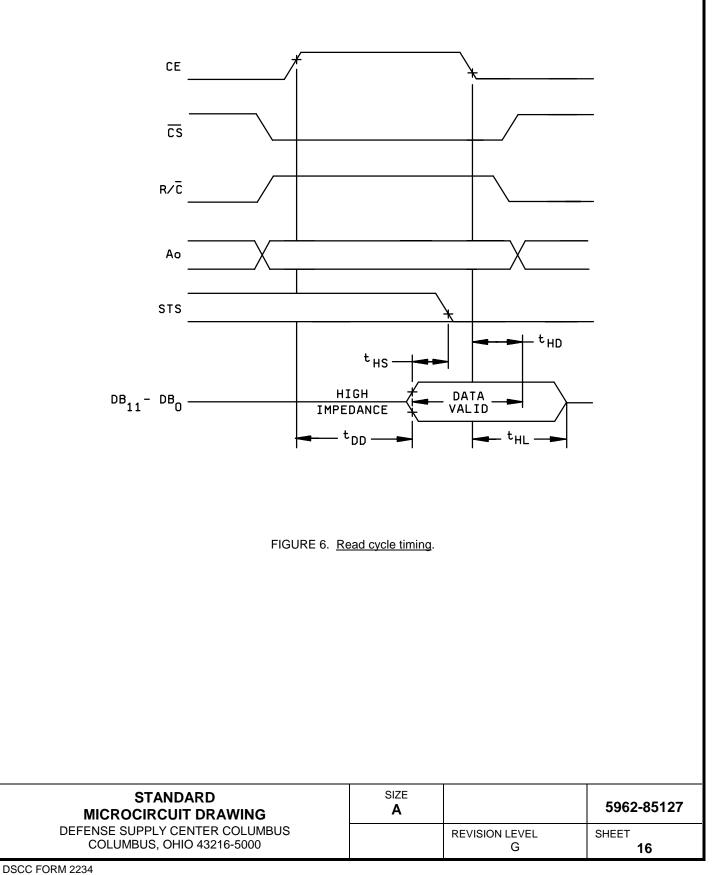


Device types 05, 06, 07, and 08









# 4. QUALITY ASSURANCE PROVISIONS

查询"5962R8512701VXA"供应商 <del>4.1\_<u>Sampling and inspection</u>. For devic</del>e classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

- 4.2.1 Additional criteria for device class M.
  - Burn-in test, method 1015 of MIL-STD-883.
    - (1) Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
    - (2)  $T_A = +125^{\circ}C$ , minimum.
  - Interim and final electrical test parameters shall be as specified in table IIA herein. b.
  - Optional subgroup 12, for device 01, is used for grading the part selection at 25°C. C.
- 4.2.2 Additional criteria for device classes Q and V.
  - The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the a. device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
  - Interim and final electrical test parameters shall be as specified in table IIA herein. b.
  - Additional screening for device class V beyond the requirements of device class Q shall be as specified in C. MIL-PRF-38535, appendix B.

4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

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### 查询"5962R8512701VXA"供应商 TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device	Device	Device
	class M	class Q	class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical	<u>1</u> /	<u>1</u> /	<u>1/, 2</u> /
parameters (see 4.2)	1, 2, 3, 4, 12	1, 2, 3, 4, 12	1, 2, 3, 4, 12
Group A test	1, 2, 3, 4, 7, 9,	1, 2, 3, 4, 7, 9,	1, 2, 3, 4, 7, 9,
requirements (see 4.4)	10, 11, 12	10, 11, 12	10, 11, 12
Group C end-point electrical parameters (see 4.4)	1, 4	1, 4	<u>2</u> / 1, 4
Group D end-point electrical parameters (see 4.4)	1, 4	1, 4	1, 4
Group E end-point electrical parameters (see 4.4)			1

1/ PDA applies to subgroup 1.

<u>2</u>/ Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be computed with reference to the previous interim electrical parameters.

TABLE IIB.	240 hour burn-in and	group C end-	point electrical	parameters.

Test title	Endpoir	nt limits	Dalta limita	Lisita
Test title	Min	Max	Delta limits	Units
Uni Vio	-1	2	<u>+</u> 0.5	LSB
Bpze	-5.5	4.5	<u>+</u> 1	LSB
Ae	-0.35	0.35	<u>+</u> .10	%FSR

4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

### 4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. For device class M, subgroups 7 tests shall be sufficient to verify the truth table. For device classes Q and V, subgroups 7 shall include verifying the functionality of the device.
- c. Subgroups 5, 6, and 8 in table I, method 5005 of MIL-STD-883 shall be omitted.
- d. Optional subgroup 12, for device type 01, is used for grading the part selection at 25°C.

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4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein. 查询"5962R8512701VXA"供应商 <del>4.4.2.1\_<u>Additional criteria for device class</u> M</u>.\_Steady-state life test conditions, method 1005 of MIL-STD-883:</del>

- a. Test condition A. B. C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- b.  $T_A = +125^{\circ}C$ , minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table IIA herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at  $T_A = +25^{\circ}C \pm 5^{\circ}C$ , after exposure, to the subgroups specified in table IIA herein.
- c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
- 5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

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### 6. NOTES

查询"5962R8512701VXA"供应商 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractorprepared specification or drawing.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.

6.4 Comments. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0547.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

### 6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

	SIZE		
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Approved sources of supply for SMD 5962-85127 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-85127013A	24355	AD574AUE/883B
5962-8512701XA	24355	AD574AUD/883B
	1ES66	MX574AUQ/883B
5962-8512701XC	1ES66	MX574AUD/883B
5962-8512701VXA	24355	AD574AUD/QMLV
5962-8512701VZA	24355	AD574AUF/QMLV
E062 85427022A	24355	AD574ATE/883B
5962-85127023A	1ES66	MX574ATE/883B
5962-8512702XA	24355	AD574ATD/883B
	1ES66	MX574ATQ/883B
5962-8512702XC	1ES66	MX574ATD/883B
5962-8512702VXA	24355	AD574ATD/QMLV
5962-8512702VZA	24355	AD574ATF/QMLV
5962R8512702VXA	24355	AD574ATD/QMLR
5962R8512702VZA	24355	AD574ATF/QMLR
5962-8512703XA	34371	HI1-574AUD/883
5962-8512703YA	34371	HI4-574AUE/883
5962-8512704XA	34371	HI1-574ATD/883
5962-8512704YA	34371	HI4-574ATE/883
5962-85127053A	<u>3</u> /	HADC574ZAMC/883
5962-8512705XC	<u>3</u> /	HADC574ZAMJ/883
5962-85127063A	<u>3</u> /	HADC574ZBMC/883
5962-8512706XC	<u>3</u> /	HADC574ZBMJ/883
5962-85127073C	<u>3</u> /	HS574AU/B-LCC
5962-8512707XC	<u>3</u> /	HS574AU/B
5962-85127083C	<u>3</u> /	HS574AT/B-LCC
5962-8512708XC	<u>3</u> /	HS574AT/B

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- <u>2</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- $\underline{3}$ / Not available from an approved source.

## 查询"5962R8512701VXA9" ( 如何的 MICROCIRCUIT DRAWING BULLETIN - continued

Vendor CAGE number	Vendor name and address
24355	Analog Devices Incorporated Route 1 Industrial Park PO Box 9106 Norwood, MA 02062-9106 Point of contact: 1500 Space Park Drive PO Box 58020 Santa Clara, CA 95050-8020
1ES66	Maxim Integrated Products 120 San Gabriel Drive Sunnyvale, CA 94086-5126
34371	Intersil Corporation 2401 Palm Bay Blvd PO Box 883 Melbourne, FL 32902-0883

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